

FORM PTO 1449 (modified) * U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			ATTY DOCKET NO. 00862.102566.		APPLICATION NO. JC17 Rec'd PCT/PTO 23 JUN 2005 101540283		
			APPLICANT KIYOFUMI SAKAGUCHI, ET AL. KUMONI				
			FILING DATE HEREWITH		GROUP 2823 NOT YET ASSIGNED		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TWP		5,221,413	06/22/93	Brasen, et al.	117	89	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
TWP	JPA	2003-78118	03/14/03	Japan	—	—	Abstract
↑	JPA	2003-78140	03/14/03	Japan	—	—	Abstract
↓	JPA	2003-178977	06/27/03	Japan	—	—	Abstract
↓	JPA	2003-282464	10/03/03	Japan	—	—	Abstract
↓	JPA	2003-282463	10/03/03	Japan	—	—	Abstract
↓	JPA	2004-342975	12/02/04	Japan	—	—	Abstract
↓	JPA	11-195562	07/21/99	Japan	—	—	Abstract
↓	JPA	07-302889	11/14/95	Japan	—	—	Abstract
TWP	EP	1248294 A2	10/09/02	EPO	—	—	
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
TWP		Current, I, Michael., et al. "Atomic-Layer Cleaving with Si ₃ Ge ₂ Strain Layers For Fabrication of Si and Ge-rich SOI Device Layers" IEEE International SOI Conference, October 1, 2001, pp. 11-12.					
↓		Shin-ichi Takagi, "Metal-Oxide-Semiconductor (MOS) device technologies using Si/Ge heretointerfaces", Oyo Buturi, Vol. 72, NO. 3, pp. 284-290, 2003.					
↓		T.A. Langdo, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 4256-4258 (2003).					
↓		D.J. Godbey, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 373-379 (1990).					
↓		D. Ferijoo, et al., J. Electro. Mat., vol. 23, no. 6, pp. 493-496 (1994).					
TWP		A.H. Krist, et al., Appl. Phys. Lett., vol. 58, no. 17, pp. 1899-1901 (1991).					
EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>05/18/2006</i>			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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